

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A thin film transistor comprising:  
an insulating layer having a first opening;  
a first conductive layer in the opening; and  
a second conductive layer on and in contact with the insulating layer and the first conductive layer,

wherein the first conductive layer is wider and thicker than the second conductive layer.

2. (Currently Amended) A thin film transistor comprising:  
an insulating layer having a first opening;  
a first conductive layer in the opening; and  
a second conductive layer on and in contact with the insulating layer and the first conductive layer,

wherein the first conductive layer is wider and thicker than the second conductive layer, and

wherein the second conductive layer is formed by a droplet discharge method using a conductive material.

3. (Currently Amended) A display device comprising:  
a first insulating layer having a first opening;  
a first conductive layer in the first opening;

a second conductive layer on and in contact with the first insulating layer and the first conductive layer;

a semiconductor layer over the second conductive layer with a gate insulating film therebetween;

a third conductive layer over the semiconductor layer;

a second insulating layer having a second opening over the third conductive layer; and a fourth conductive layer in the second opening,

wherein the first conductive layer is wider and thicker than the second conductive layer, and

wherein the fourth conductive layer is thicker than the third conductive layer.

4. (Currently Amended) A display device comprising:

a first insulating layer having a first opening;

a first conductive layer in the first opening;

a second conductive layer on and in contact with the first insulating layer and the first conductive layer;

a semiconductor layer over the second conductive layer with a gate insulating film therebetween;

a third conductive layer over the semiconductor layer;

a second insulating layer having a second opening over the third conductive layer; and a fourth conductive layer in the second opening,

wherein the first conductive layer is wider and thicker than the second conductive layer,

wherein the fourth conductive layer is thicker than the third conductive layer, and

wherein each of the second conductive layer and the third conductive layer is formed by a droplet discharge method using a conductive material.

5. (Currently Amended) A display device comprising:

a first insulating layer having a first opening;

a first conductive layer in the first opening;

a second conductive layer on and in contact with the first insulating layer and the first conductive layer;

a semiconductor layer over the second conductive layer with a gate insulating film therebetween;

a pair of third conductive layers over the semiconductor layer;

a first electrode over one of the pair of third conductive layers;

an electroluminescent layer over the first electrode; and

a second electrode over the electroluminescent layer,

wherein the first conductive layer is wider and thicker than the second conductive layer.

6. (Currently Amended) A display device comprising

a first insulating layer having a first opening;

a first conductive layer in the first opening;

a second conductive layer on and in contact with the first insulating layer and the first conductive layer;

a semiconductor layer over the second conductive layer with a gate insulating film therebetween;

a pair of third conductive layers over the semiconductor layer;  
a first electrode over one of the pair of third conductive layers;  
an electroluminescent layer over the first electrode; and  
a second electrode over the electroluminescent layer,  
wherein the first conductive layer is wider and thicker than the second conductive layer, and  
wherein the second conductive layer is formed by a droplet discharge method using a conductive material.

7. (Currently Amended) A display device comprising:  
a first insulating layer having a first opening;  
a first conductive layer in the first opening;  
a second conductive layer on and in contact with the insulating layer and the first conductive layer;  
a semiconductor layer over the second conductive layer with a gate insulating film therebetween;  
a pair of third conductive layers over the semiconductor layer;  
a first electrode over one of the pair of third conductive layers;  
a second insulating layer having a second opening over the other one of the pair of third conductive layers;  
a fourth conductive layer in the second opening;  
an electroluminescent layer over the first electrode; and  
a second electrode over the electroluminescent layer,

wherein the first conductive layer is wider and thicker than the second conductive layer, and

wherein the fourth conductive layer is thicker than the pair of [[the]] third conductor layer layers.

8. (Currently Amended) A display device comprising:

- a first insulating layer having a first opening;
- a first conductive layer in the first opening;
- a second conductive layer on and in contact with the first insulating layer and the first conductive layer;
- a semiconductor layer over the second conductive layer with a gate insulating film therebetween;
- a pair of third conductive layers over the semiconductor layer;
- a first electrode over one of the pair of third conductive layers;
- a second insulating layer having a second opening over the other one of the pair of third conductive layers;
- a fourth conductive layer in the second opening;
- an electroluminescent layer over the first electrode; and
- a second electrode over the electroluminescent layer,

wherein the first conductive layer is wide and thicker than the second conductive layer,

wherein the fourth conductive layer is thicker than the pair of [[the]] third conductive layer layers, and

wherein each of the second conductive layer and the third conductive layer is formed by a droplet discharge method using a conductive material.

9. (Original) The thin film transistor or the display device according to any one of claims 1 to 8, wherein the thin film transistor or the display device further comprises a titanium oxide film below the first conductive layer.

10. (Original) The thin film transistor or the display device according to any one of claims 1 to 8, wherein the thin film transistor or the display device further comprises a film comprising at least one selected from the group consisting of W (tungsten), Al (aluminum), Ta (tantalum), Zr (zirconium), Hf (hafnium), Ir (iridium), Nb (niobium), Pd (lead), Pt (platinum), Mo (molybdenum), Rh (rhodium), Sc (scandium), Ti (titanium), V (vanadium), Cr (chromium), Mn (manganese), Fe (iron), Co (cobalt), Ni (nickel), Cu (copper), and Zn (zinc) below the first conductive layer.

11. (Original) The thin film transistor or the display device according to any one of claims 1 to 8, wherein the second conductive layer includes at least one of silver, gold, copper, and indium tin oxide.

12. (Original) The display device according to any one of claims 3 to 8, wherein the third conductive layer includes at least one of silver, gold, copper, and indium tin oxide.

13. (Original) The thin film transistor or the display device according to any one of claims 1 to 8, wherein a width of the first opening is from 5  $\mu\text{m}$  to 100  $\mu\text{m}$ .

14. (Original) The display device according to any one of claims 3 to 8, wherein the semiconductor layer is an amorphous semiconductor layer including at least one of hydrogen and halogen.

15. (Previously Presented) The display device according to any one of claims 3 to 8, wherein the semiconductor layer is a semi-amorphous semiconductor layer including at least one of hydrogen and halogen.

16. (Original) The display device according to any one of claims 3 to 8, wherein the semiconductor layer is a polycrystalline semiconductor including at least one of hydrogen and halogen.

17. (Original) The display device according to any one of claims 3 to 8, wherein a channel length of the semiconductor layer is from 5  $\mu\text{m}$  to 100  $\mu\text{m}$ .

18. (Original) A television apparatus including the display device according to any one of claims 3 to 8 as a display screen.

19. (Original) A television apparatus including a display device with the thin film transistor according to claims 1 or 2 as a display screen.

20.-32. (Canceled)